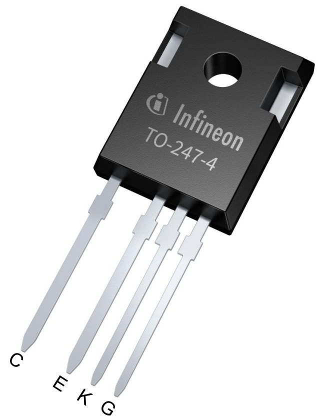
CoolSiC™ Hybrid Discrete - TRENCHSTOP™ 5 H5 IGBT co-packed with half-rated 6th generation CoolSiC™ diode



Features

- V_{CE} = 650 V
- I_C = 50 A
- Ultra-low switching losses due to the combination of TRENCHSTOP™ 5 and CoolSiC™ technology as well as the Kelvin emitter pin
- Benchmark efficiency in hard switching topologies
- Plug-and-play replacement of pure silicon devices
- Simplified PCB design due to the optimized pin-out of the four-pin package
- Improved wave soldering quality due to the increased clearance of the Kelvin emitter and gate pins
- Maximum junction temperature T_{vjmax} = 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/

Lead-free
Green
Halogen-free
RoHS

Potential applications

- Industrial SMPS
- Industrial UPS
- Solar string inverter
- Energy storage
- Charger

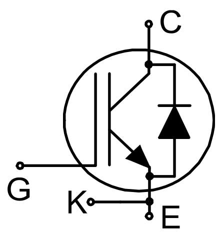
Product validation

- Qualified for applications listed above based on the test conditions in the relevant tests of JEDEC20/22

Description

Package pin definition:

- Pin C & backside - collector
- Pin E - emitter
- Pin K - Kelvin emitter
- Pin G - gate



Type	Package	Marking
IKZA50N65RH5	PG-TO247-4-3	K50ERH5

Table of contents

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25$ °C		650	V
DC collector current, limited by T_{vjmax}	I_C	limited by bondwire	$T_c = 25$ °C	80	A
			$T_c = 100$ °C	56	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			200	A
Turn-off safe operating area		$V_{CE} \leq 650$ V, $t_p = 1$ µs, $T_{vj} \leq 175$ °C		200	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 10$ µs, $D < 0.01$		±30	V
Power dissipation	P_{tot}		$T_c = 25$ °C	305	W
			$T_c = 100$ °C	152.5	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 50$ A, $V_{GE} = 15$ V	$T_{vj} = 25$ °C		1.65	2.1	V
			$T_{vj} = 125$ °C		1.85		
			$T_{vj} = 175$ °C		1.95		
Gate-emitter threshold voltage	V_{GEth}	$I_C = 0.5$ mA, $V_{CE} = V_{GE}$		3.2	4	4.8	V

(table continues...)

Table 3 **(continued) Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Zero gate-voltage collector current	I_{CES}	V_{CE} = 650 V, V_{GE} = 0 V	T_{vj} = 25 °C			700	µA
			T_{vj} = 175 °C		2000		
Zero gate-voltage collector current	I_{CES}	V_{CE} = 480 V, V_{GE} = 0 V	T_{vj} = 25 °C			25	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V				100	nA
Transconductance	g_{fs}	I_C = 50 A, V_{CE} = 20 V			62		S
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 250 kHz			2660		pF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 250 kHz			320		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 250 kHz			10		pF
Gate charge	Q_G	I_C = 50 A, V_{GE} = 15 V, V_{CC} = 520 V			120		nC
Turn-on delay time	$t_{d(on)}$	V_{CC} = 400 V, V_{GE} = 0/15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, $L_σ$ = 30 nH, $C_σ$ = 30 pF	T_{vj} = 25 °C, I_C = 25 A		21		ns
			T_{vj} = 25 °C, I_C = 5 A		19		
			T_{vj} = 150 °C, I_C = 25 A		20		
			T_{vj} = 150 °C, I_C = 5 A		18		
Rise time (inductive load)	t_r	V_{CC} = 400 V, V_{GE} = 0/15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, $L_σ$ = 30 nH, $C_σ$ = 30 pF	T_{vj} = 25 °C, I_C = 25 A		6		ns
			T_{vj} = 25 °C, I_C = 5 A		3		
			T_{vj} = 150 °C, I_C = 25 A		7		
			T_{vj} = 150 °C, I_C = 5 A		3		
Turn-off delay time	$t_{d(off)}$	V_{CC} = 400 V, V_{GE} = 0/15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, $L_σ$ = 30 nH, $C_σ$ = 30 pF	T_{vj} = 25 °C, I_C = 25 A		180		ns
			T_{vj} = 25 °C, I_C = 5 A		200		
			T_{vj} = 150 °C, I_C = 25 A		200		
			T_{vj} = 150 °C, I_C = 5 A		250		

(table continues...)

Table 3 **(continued) Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Fall time (inductive load)	t_f	V_{CC} = 400 V, V_{GE} = 0/15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, $L_σ$ = 30 nH, $C_σ$ = 30 pF	T_{vj} = 25 °C, I_C = 25 A		18		ns
			T_{vj} = 25 °C, I_C = 5 A		25		
			T_{vj} = 150 °C, I_C = 25 A		25		
			T_{vj} = 150 °C, I_C = 5 A		35		
Turn-on energy	E_{on}	V_{CC} = 400 V, V_{GE} = 0/15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, $L_σ$ = 30 nH, $C_σ$ = 30 pF	T_{vj} = 25 °C, I_C = 25 A		0.2		mJ
			T_{vj} = 25 °C, I_C = 5 A		0.05		
			T_{vj} = 150 °C, I_C = 25 A		0.27		
			T_{vj} = 150 °C, I_C = 5 A		0.08		
Turn-off energy	E_{off}	V_{CC} = 400 V, V_{GE} = 0/15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, $L_σ$ = 30 nH, $C_σ$ = 30 pF	T_{vj} = 25 °C, I_C = 25 A		0.18		mJ
			T_{vj} = 25 °C, I_C = 5 A		0.05		
			T_{vj} = 150 °C, I_C = 25 A		0.27		
			T_{vj} = 150 °C, I_C = 5 A		0.08		
Total switching energy	E_{ts}	V_{CC} = 400 V, V_{GE} = 0/15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, $L_σ$ = 30 nH, $C_σ$ = 30 pF	T_{vj} = 25 °C, I_C = 25 A		0.38		mJ
			T_{vj} = 25 °C, I_C = 5 A		0.1		
			T_{vj} = 150 °C, I_C = 25 A		0.54		
			T_{vj} = 150 °C, I_C = 5 A		0.16		
IGBT thermal resistance, junction-case	$R_{th(j-c)}$					0.5	K/W
Operating junction temperature	T_{vj}			-40		175	°C

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} \geq 25$ °C		650	V
Diode forward current, limited by T_{vjmax}	I_F		$T_c = 25$ °C	33.7	A
			$T_c = 100$ °C	22.8	
Diode pulsed current, t_p limited by T_{vjmax} [1)]	I_{Fpulse}			75	A

1) Pulse current level depends on T_{vj} of diode chip, see also Fig. "Maximum pulse current as a function of junction temperature"

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 20$ A	$T_{vj} = 25$ °C		1.35	1.5	V
			$T_{vj} = 125$ °C		1.55		
			$T_{vj} = 175$ °C		1.65		
Diode thermal resistance, junction-case	$R_{th(j-c)}$					1.5	K/W
Operating junction temperature	T_{vj}			-40		175	°C

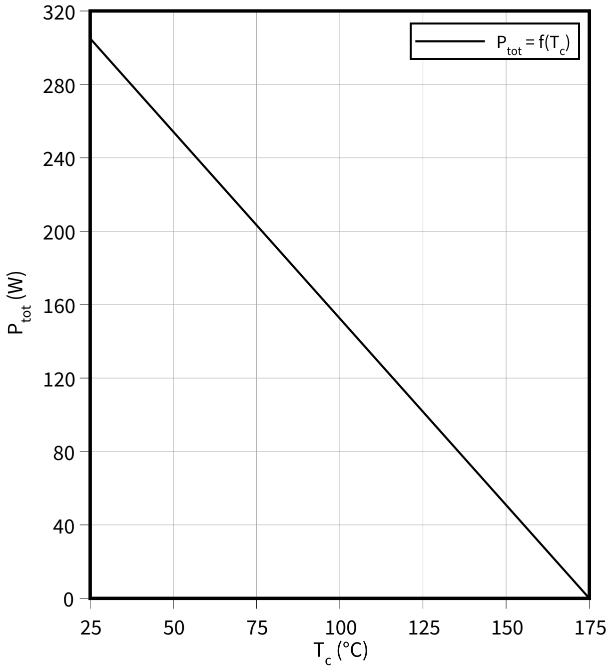
Note: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*

Electrical Characteristic at T_{vj} = 25°C, unless otherwise specified.

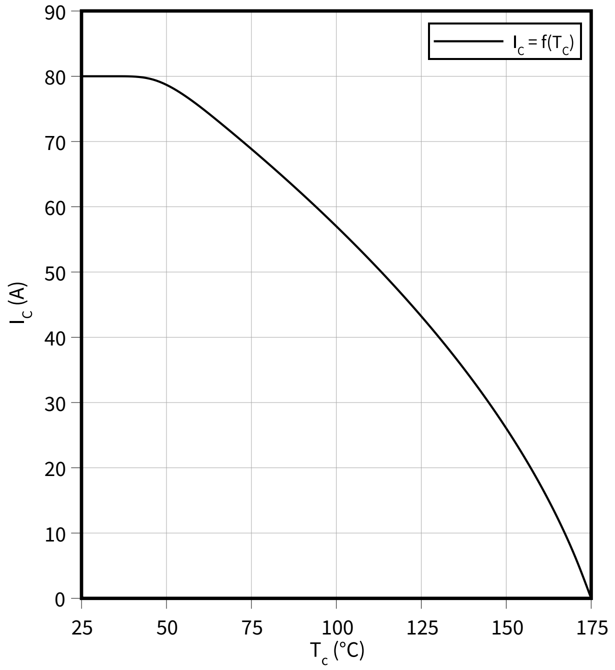
Dynamic test circuit, parasitic inductance L_σ, parasitic capacitor C_σ from Fig. E. Energy losses include "tail" and diode reverse recovery.

4 Characteristics diagrams

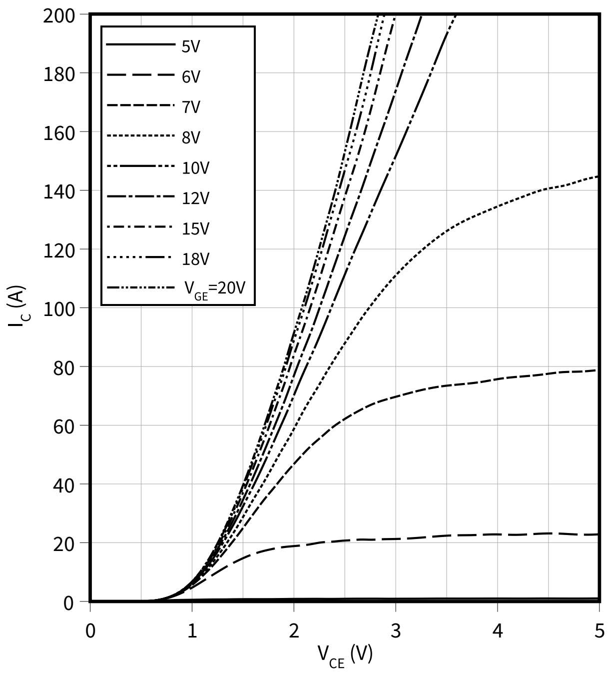
Power dissipation as a function of case temperature
$P_{tot} = f(T_c)$
$T_{vj} \leq 175$ °C



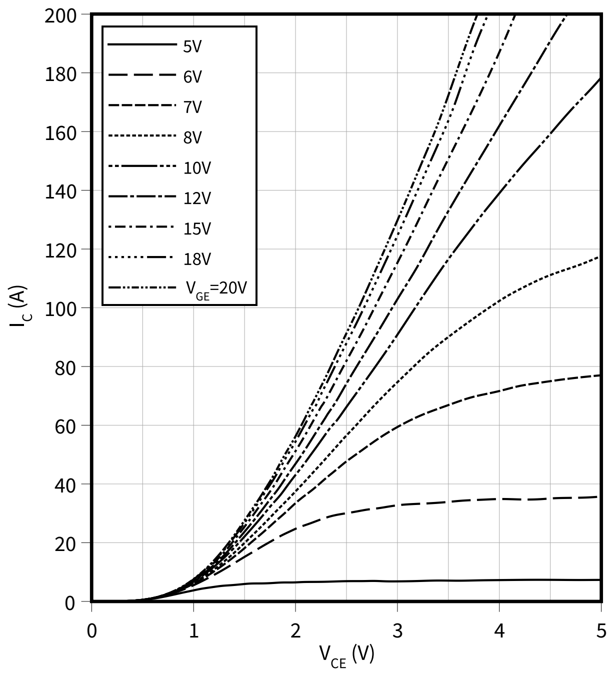
Collector current as a function of case temperature
$I_C = f(T_c)$
$T_{vj} \leq 175$ °C, $V_{GE} \geq 15$ V



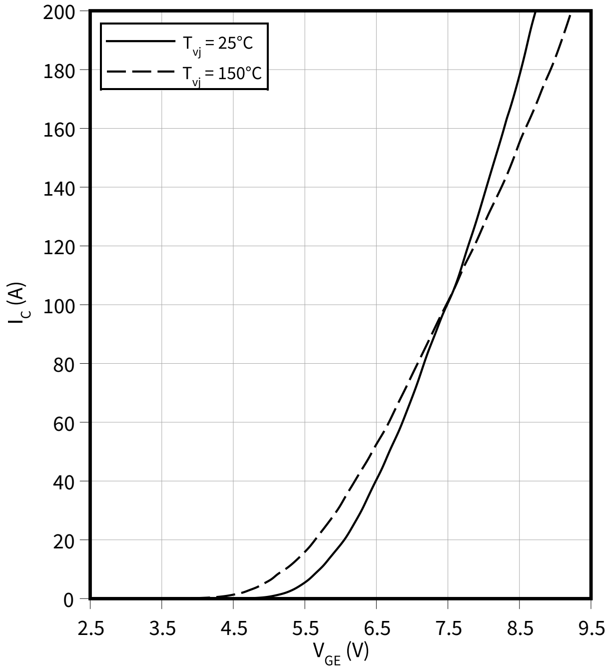
Typical output characteristic
$I_C = f(V_{CE})$
$T_{vj} = 25$ °C



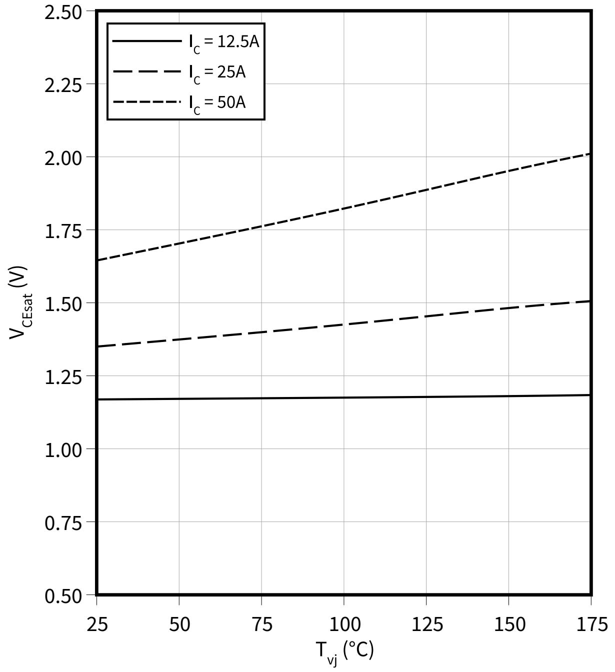
Typical output characteristic
$I_C = f(V_{CE})$
$T_{vj} = 150$ °C



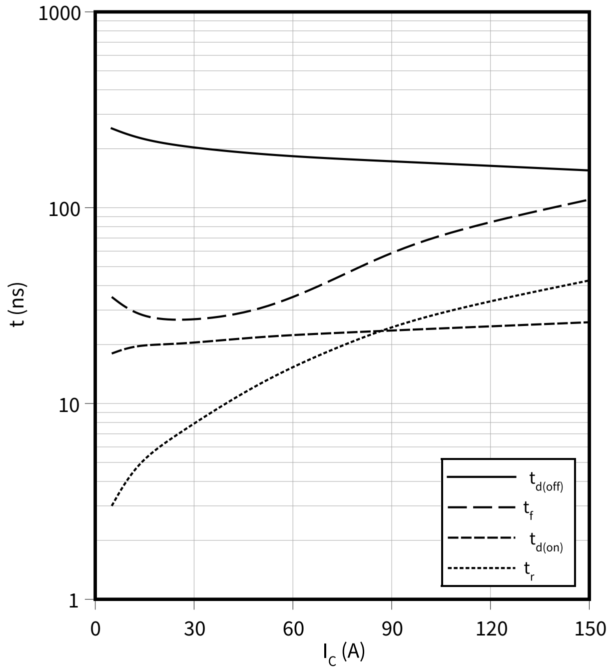
Typical transfer characteristic
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



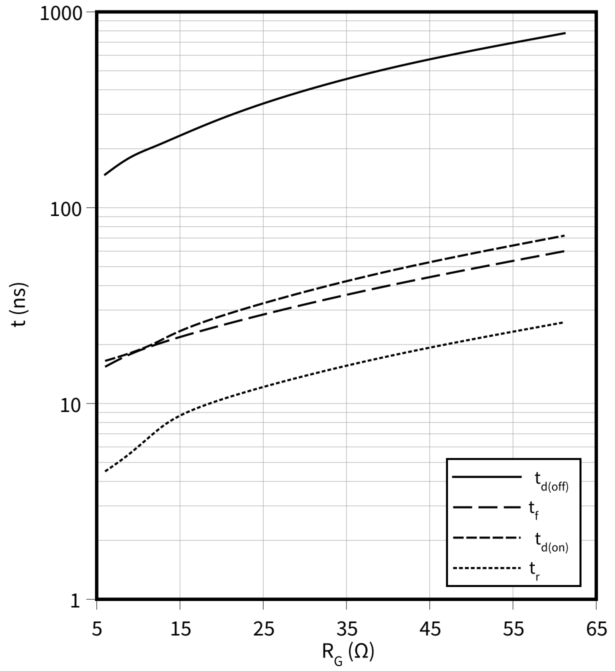
Typical collector-emitter saturation voltage as a function of junction temperature
$V_{CEsat} = f(T_{vj})$
$V_{GE} = 15$ V



Typical switching times as a function of collector current
$t = f(I_C)$
$V_{CC} = 400$ V, $T_{vj} = 150$ °C, $V_{GE} = 0/15$ V, $R_G = 12\ \Omega$



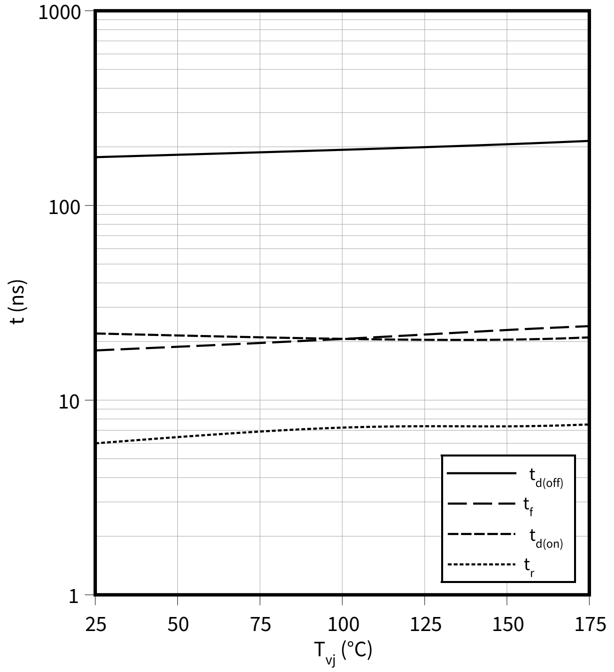
Typical switching times as a function of gate resistor
$t = f(R_G)$
$I_C = 25$ A, $V_{CC} = 400$ V, $T_{vj} = 150$ °C, $V_{GE} = 0/15$ V



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

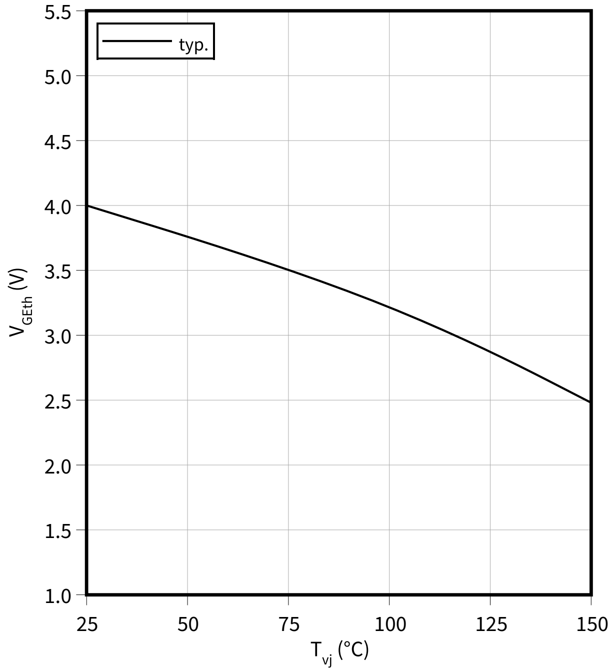
$I_C = 25$ A, $V_{CC} = 400$ V, $V_{GE} = 0/15$ V, $R_G = 12$ Ω



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

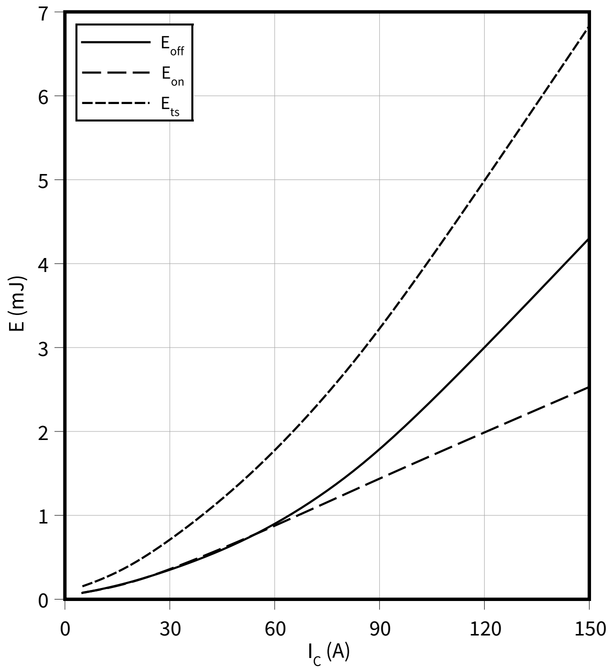
$I_C = 0.5$ mA



Typical switching energy losses as a function of collector current

$E = f(I_C)$

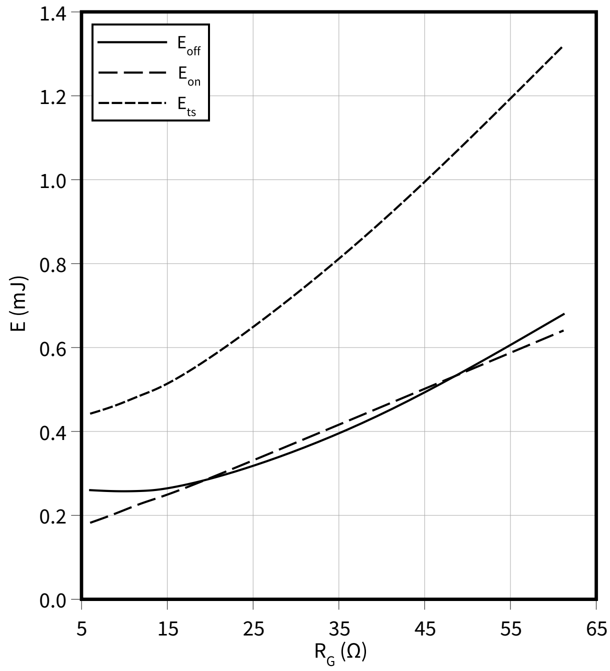
$V_{CC} = 400$ V, $T_{vj} = 150$ °C, $V_{GE} = 0/15$ V, $R_G = 12$ Ω



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

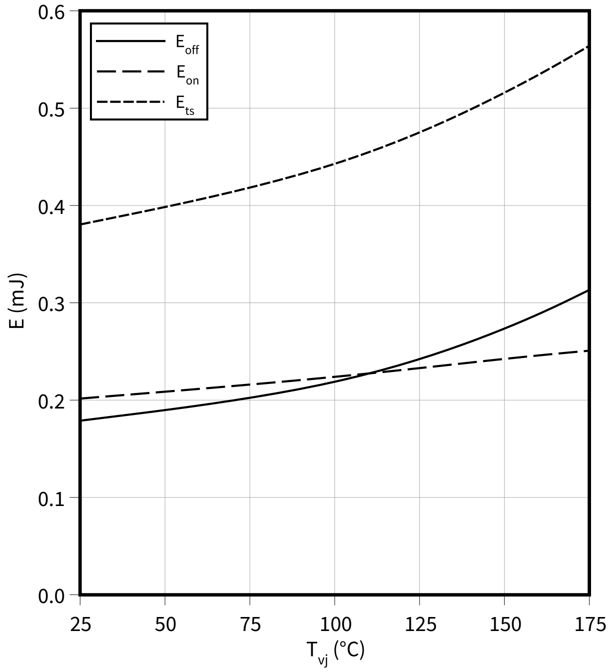
$I_C = 25$ A, $V_{CC} = 400$ V, $T_{vj} = 150$ °C, $V_{GE} = 0/15$ V



Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

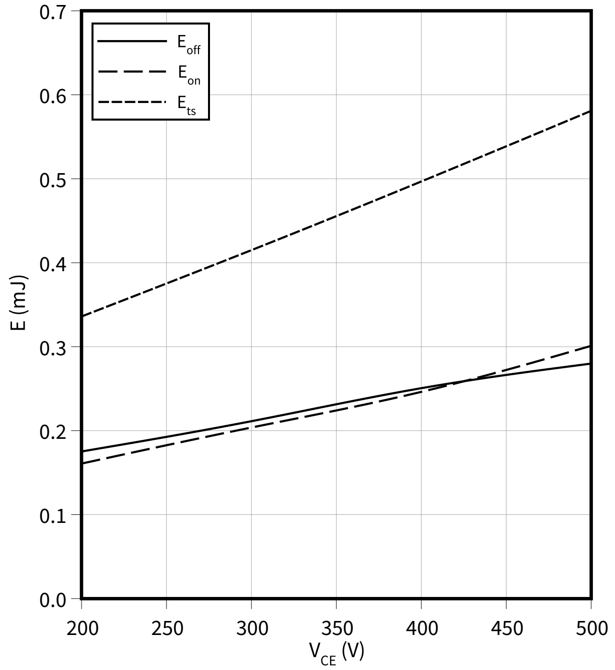
$I_C = 25$ A, $V_{CC} = 400$ V, $V_{GE} = 0/15$ V, $R_G = 12\ \Omega$



Typical switching energy losses as a function of collector emitter voltage

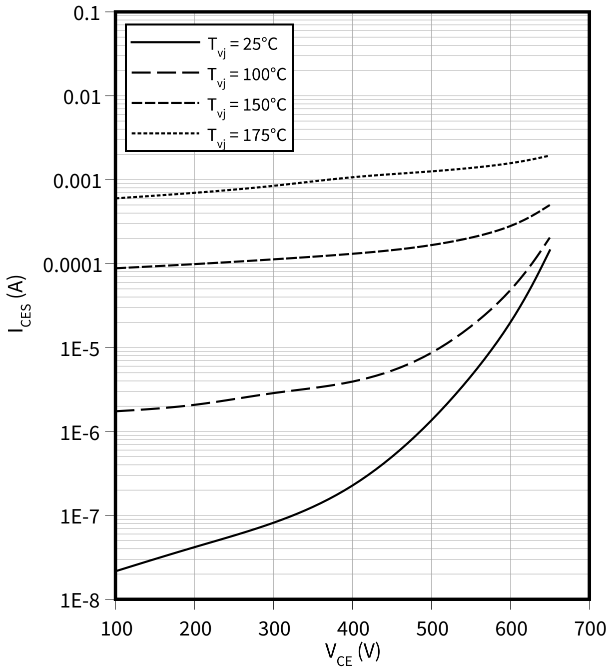
$E = f(V_{CE})$

$I_C = 25$ A, $T_{vj} = 150$ °C, $V_{GE} = 0/15$ V, $R_G = 12\ \Omega$



Typ. reverse current vs. reverse voltage as a function of Tvj

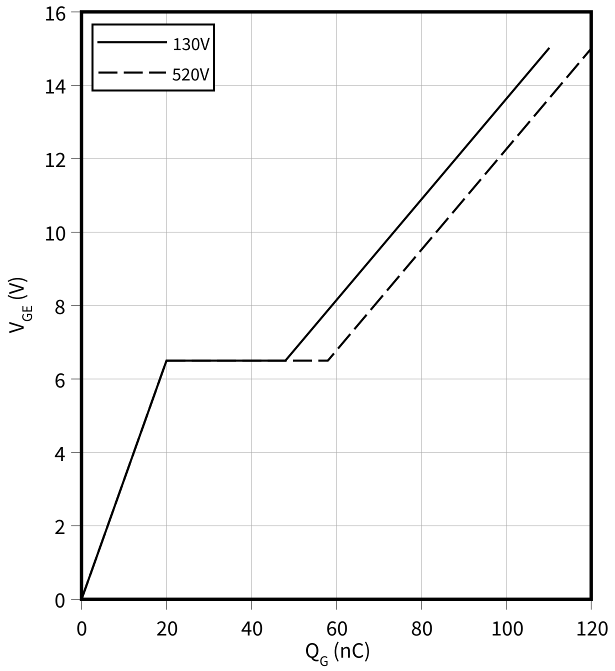
$I_{CES} = f(V_{CE})$



Typical gate charge

$V_{GE} = f(Q_G)$

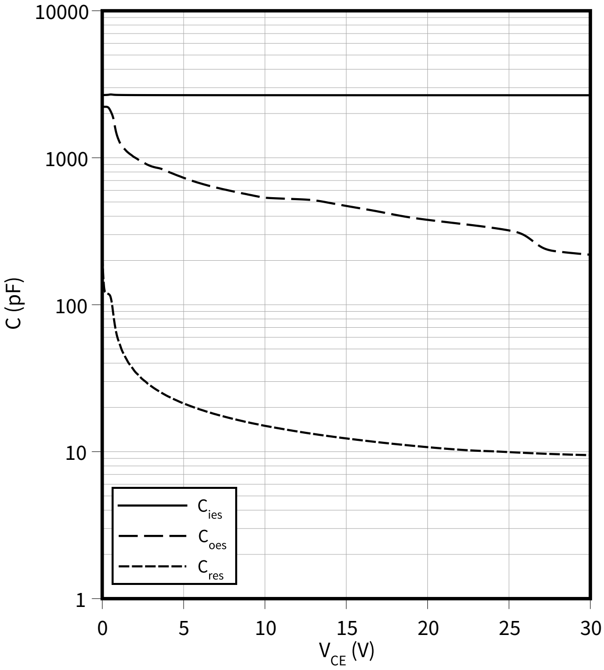
$I_C = 50$ A



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

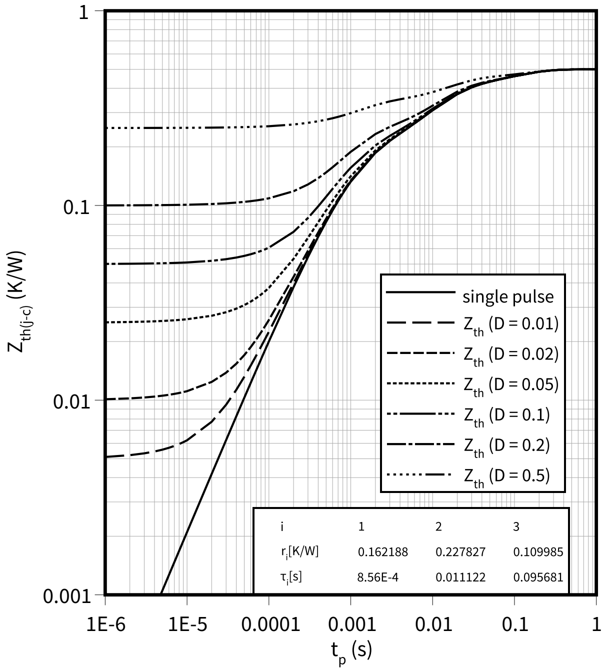
$f = 250$ kHz, $V_{GE} = 0$ V



IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

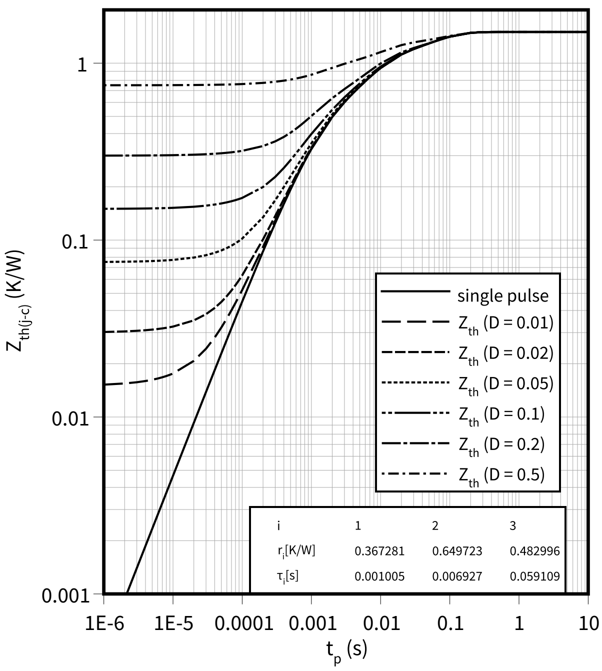
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width

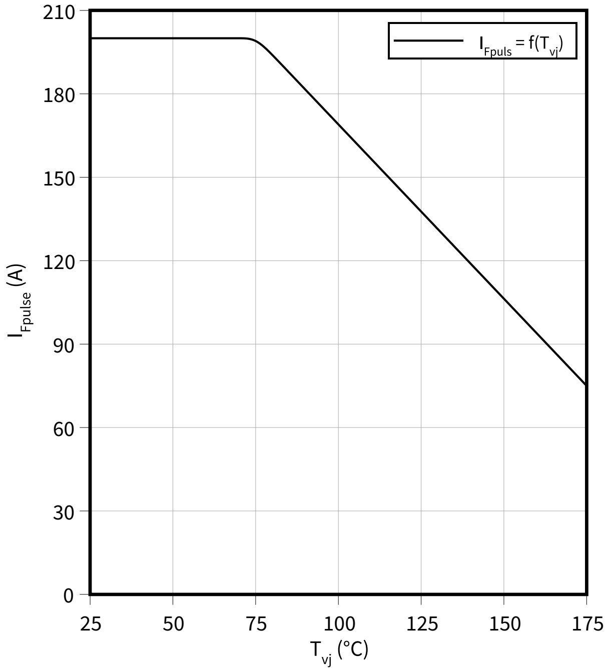
$Z_{th(j-c)} = f(t_p)$

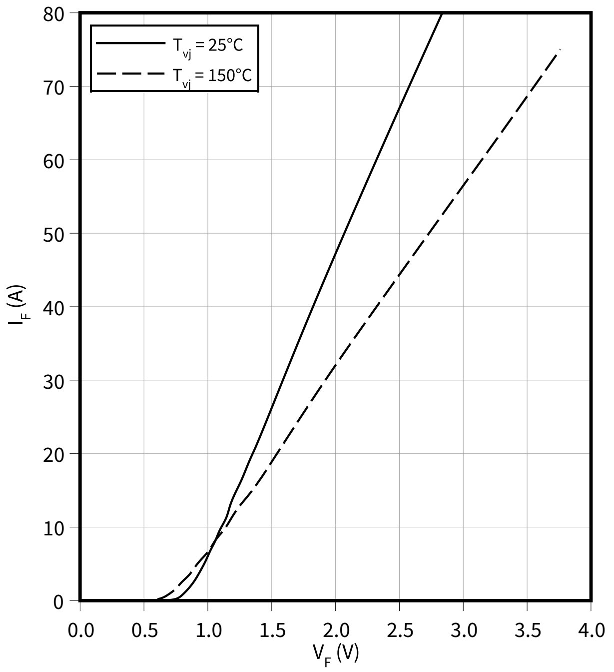
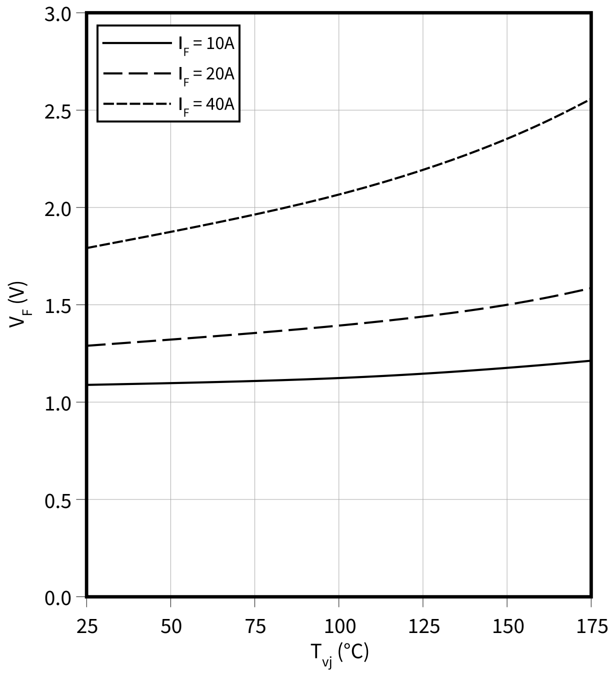
$D = t_p/T$



Maximum pulse current as a function of junction temperature

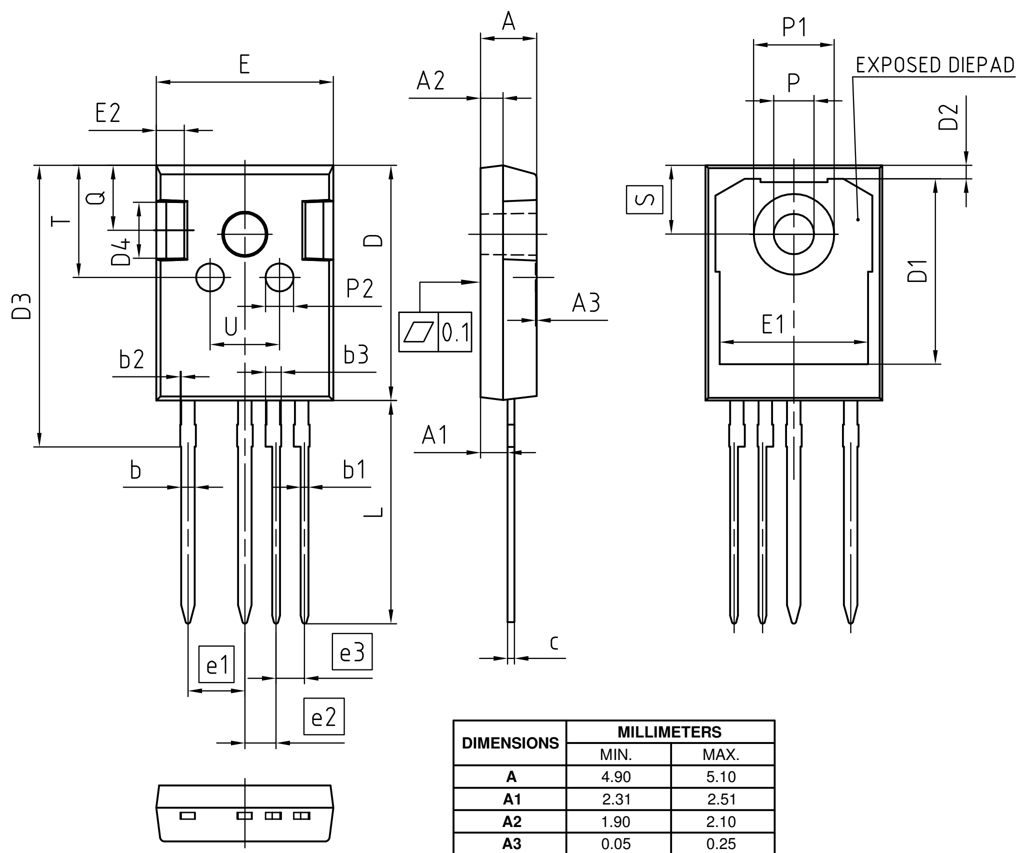
$I_{Fpulse} = f(T_{vj})$



Typical diode forward current as a function of forward voltage $I_F = f(V_F)$	**Typical diode forward voltage as a function of junction temperature** $V_F = f(T_{vj})$
	

5 Package outlines

PG-TO247-4-3



NOTES:
ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.90	5.10
A1	2.31	2.51
A2	1.90	2.10
A3	0.05	0.25
b	1.10	1.30
b1	0.65	0.79
b2	-	0.20
b3	1.34	1.44
c	0.58	0.66
D	20.90	21.10
D1	16.25	16.85
D2	1.05	1.35
D3	24.97	25.27
D4	4.90	5.10
E	15.70	15.90
E1	13.10	13.50
E2	2.40	2.60
e1	5.08	
e2	2.79	
e3	2.54	
L	19.80	20.10
L1	-	4.30
øP	3.50	3.70
øP1	7.00	7.40
øP2	2.40	2.60
Q	5.60	6.00
S	6.15	
T	9.80	10.20
U	6.00	6.40

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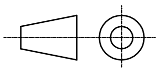
Z8B00184785

REVISION
03

SCALE 2:1
0 5 10mm

EUROPEAN PROJECTION



ISSUE DATE
21.08.2017

Figure 1

6 Testing conditions

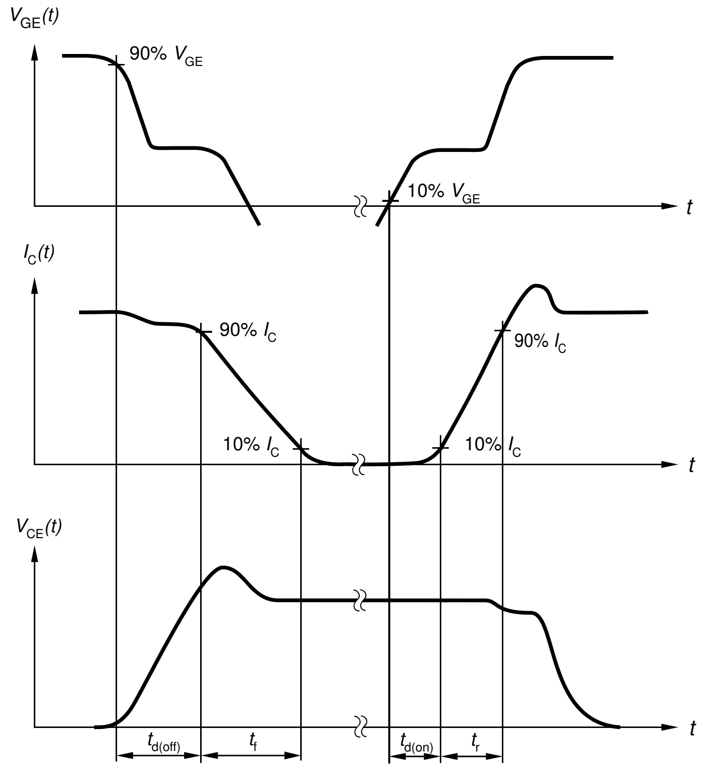


Figure A. **Definition of switching times**

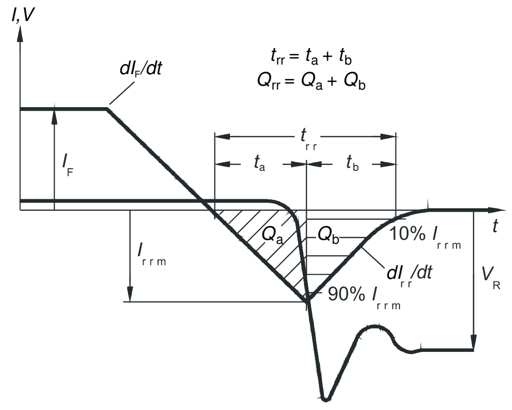


Figure C. **Definition of diode switching characteristics**

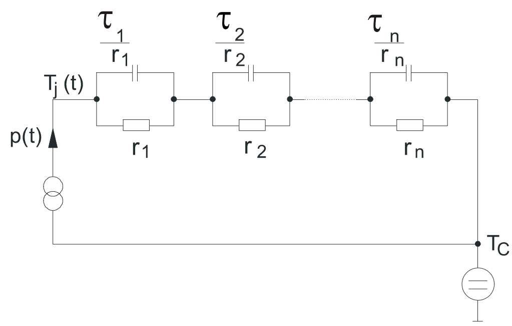


Figure D. **Thermal equivalent circuit**

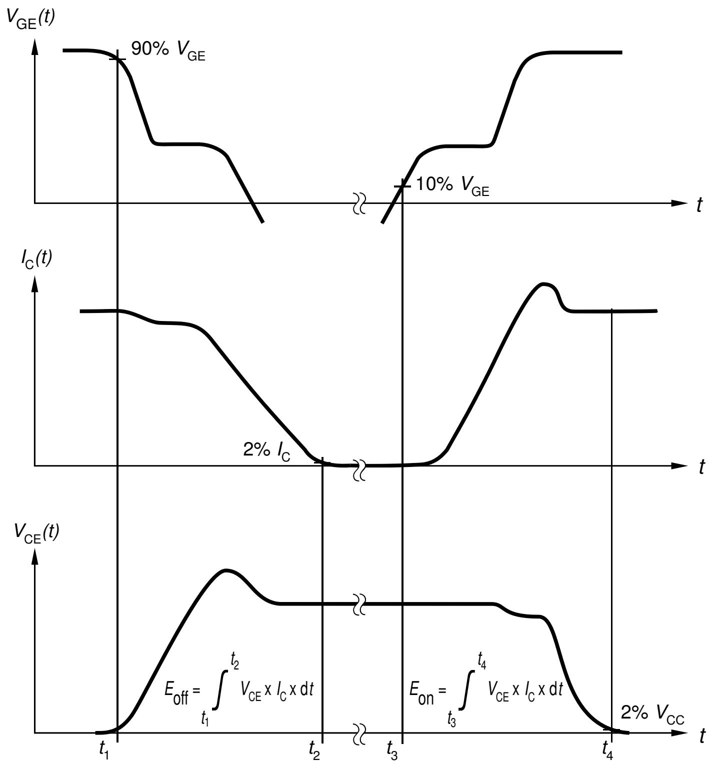


Figure B. **Definition of switching losses**

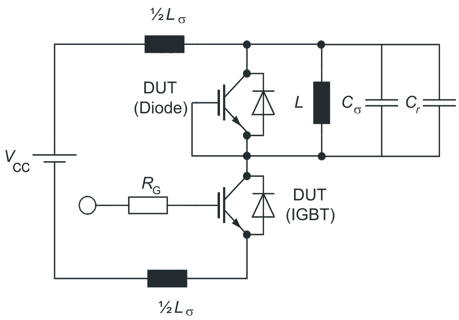


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

Figure 2

Revision history

Document revision	Date of release	Description of changes
V1.1	2020-03-20	Preliminary Data Sheet
V2.1	2020-07-27	Final Data Sheet
n/a	2020-11-30	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2022-09-22	Rename of product family name from “Hybrid CoolSiC™ IGBT” to “CoolSiC™ hybrid discrete” Corrected the values in table of $Z_{th} = f(t_p)$ diode diagram

Trademarks

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Email: erratum@infineon.com

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